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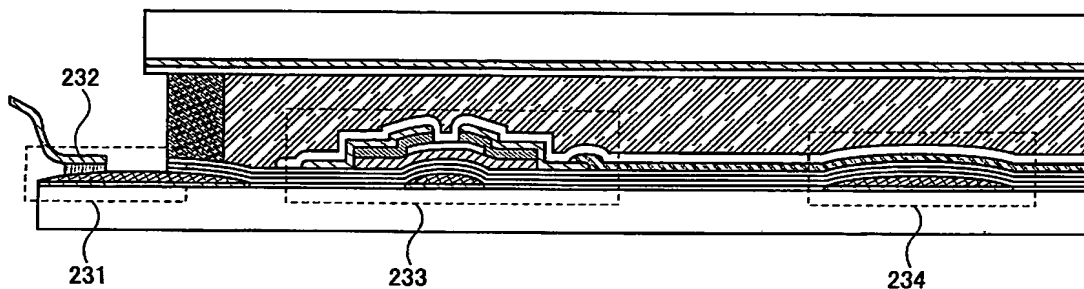
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(54) Title: METHOD FOR MANUFACTURING LIQUID CRYSTAL DISPLAY DEVICE



(57) Abstract: A conventionally followed technique of manufacturing a liquid crystal display device is a method for forming various types of coatings over an entire surface of a substrate and for removing the coatings with a small region left by etching, which requires wasting a material cost and treating a large quantity of waste. A liquid crystal display device is manufactured by forming at least one or more of patterns necessary for manufacturing a liquid crystal display device by a method capable of selectively forming a pattern. A droplet discharge method capable of forming a predetermined pattern by selectively discharging a droplet of a composition prepared for a specific purpose is employed as the method capable of selectively forming a pattern.

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